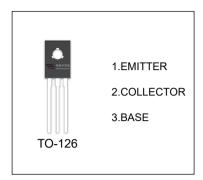


## **B772** TRANSISTOR (PNP)

### **FEATURES**

■ Low Speed Switching



#### **ORDERING INFORMATION**

Part Number	Package	Packing Method	Pack Quantity
B772	TO-126	Bulk	200pcs/Bag
B772-TU	TO-126	Tube	60pcs/Tube

# 

Symbol	Parameter		Unit
V <sub>CBO</sub>	Collector-Base Voltage	-40	V
V <sub>CEO</sub>	Collector-Emitter Voltage		V
V <sub>EBO</sub>	Emitter-Base Voltage	-6	V
Ic	Collector Current -Continuous	-3	Α
Pc	Collector Power Dissipation	1.25	W
R <sub>OJA</sub>	Thermal Resistance from Junction to Ambient		°C/W
T <sub>J</sub> ,T <sub>stg</sub>	Operation Junction and Storage Temperature Range	-55-150	°C



# $T_a$ =25 $^{\circ}$ C unless otherwise specified

Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> =-100μA ,I <sub>E</sub> =0	-40			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> = -10mA , I <sub>B</sub> =0	-30			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> = -100μΑ,I <sub>C</sub> =0	-6			V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> = -40V, I <sub>E</sub> =0			-1	μA
Collector cut-off current	I <sub>CEO</sub>	V <sub>CE</sub> =-30V, I <sub>B</sub> =0			-10	μA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =-6V, I <sub>C</sub> =0			-1	μA
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> = -2V, I <sub>C</sub> = -1A	60		400	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =-2A, I <sub>B</sub> = -0.2A			-0.5	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =-2A, I <sub>B</sub> = -0.2A			-1.5	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> = -5V, I <sub>C</sub> =-0.1A f =10MHz	50	80		MHz

## **CLASSIFICATION OF hfe**

Rank	R	0	Υ	GR
Range	60-120	100-200	160-320	200-400



